

TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

262,144-WORD BY 8-BIT STATIC RAM

**DESCRIPTION**

The TC55V2001FI/FTI/TRI/STI/SRI is a 2,097,152-bit static random access memory (SRAM) organized as 262,144 words by 8 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 2.7 to 3.6 V power supply. Advanced circuit technology provides both high speed and low power at an operating current of 3 mA/MHz and a minimum cycle time of 85 ns. It is automatically placed in low-power mode at 1  $\mu$ A standby current (L-Version at  $V_{DD}=3V$ ,  $T_a=25^\circ C$ ) when chip enable ( $\overline{CE1}$ ) is asserted high or ( $\overline{CE2}$ ) is asserted low. There are three control inputs.  $\overline{CE1}$  and  $\overline{CE2}$  are used to select the device and for data retention control, and output enable ( $\overline{OE}$ ) provides fast memory access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. The TC55V2001FI/FTI/TRI/STI/SRI is available in a plastic 32-pin small-outline package (SOP) and normal and reverse pinout plastic 32-pin thin-small-outline package (TSOP).

**FEATURES**

- Low-power dissipation  
Operating: 10.8 mW/MHz (typical)
- Single power supply voltage of 2.7 to 3.6 V
- Power down features using  $\overline{CE1}$  and  $\overline{CE2}$ .
- Data retention supply voltage of 2 to 3.6 V
- Direct TTL compatibility for all inputs and outputs
- Standby current ( $T_a=25^\circ C$  maximum)

	TC55V2001FI/FTI/TRI/STI/SRI	
	-85, -10	-85L, -10L
3.6V	3 $\mu$ A	1.4 $\mu$ A
3.0V	2 $\mu$ A	1 $\mu$ A

- Access Times (maximum):

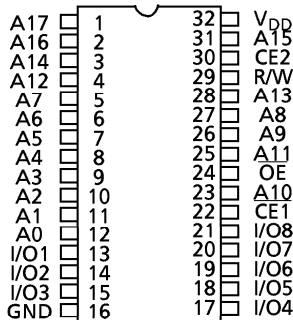
	TC55V2001FI/FTI/TRI/STI/SRI	
	-85, -85L	-10, -10L
Access Time	85ns	100ns
$\overline{CE1}$ Access Time	85ns	100ns
$\overline{CE2}$ Access Time	85ns	100ns
$\overline{OE}$ Access Time	45ns	50ns

- Packages:

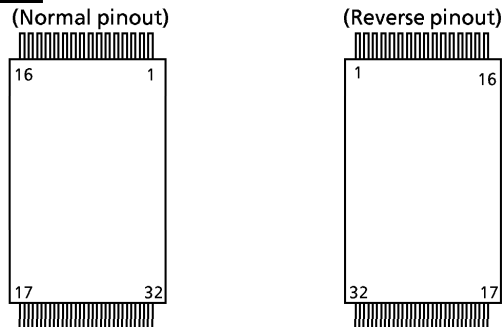
- SOP32-P-525-1.27 (FI) (Weight: 1.06 g typ)
- TSOP I 32-P-0820-0.50 (FTI) (Weight: 0.34 g typ)
- TSOP I 32-P-0820-0.50A (TRI) (Weight: 0.34 g typ)
- TSOP I 32-P-0.50 (STI) (Weight: 0.24 g typ)
- TSOP I 32-P-0.50A (SRI) (Weight: 0.24 g typ)

**PIN ASSIGNMENT (TOP VIEW)**

○ 32 PIN SOP



○ 32 PIN TSOP



**PIN NAMES**

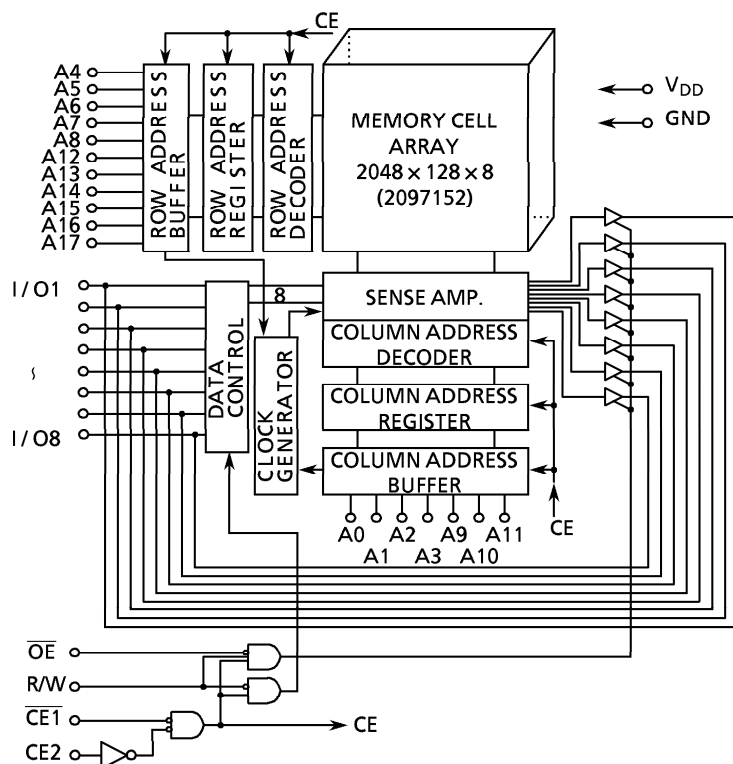
A0 to A17	Address Inputs
R/W	Read / Write Control Input
$\overline{OE}$	Output Enable Input
$\overline{CE1}, \overline{CE2}$	Chip Enable Input
I/O1 to I/O8	Data Input / Output
$V_{DD}$	Power
GND	Ground

PIN NO.	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
PIN NAME	A <sub>11</sub>	A <sub>9</sub>	A <sub>8</sub>	A <sub>13</sub>	R/W	CE2	A <sub>15</sub>	$V_{DD}$	A <sub>17</sub>	A <sub>16</sub>	A <sub>14</sub>	A <sub>12</sub>	A <sub>7</sub>	A <sub>6</sub>	A <sub>5</sub>	A <sub>4</sub>
PIN NO.	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32
PIN NAME	A <sub>3</sub>	A <sub>2</sub>	A <sub>1</sub>	A <sub>0</sub>	I/O1	I/O2	I/O3	GND	I/O4	I/O5	I/O6	I/O7	I/O8	$\overline{CE1}$	A <sub>10</sub>	$\overline{OE}$

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**BLOCK DIAGRAM**



**OPERATION MODE**

MODE	$\overline{CE1}$	CE2	$\overline{OE}$	R/W	I/O1 to I/O8	POWER
Read	L	H	L	H	D <sub>OUT</sub>	I <sub>DDO</sub>
Write	L	H	x	L	D <sub>IN</sub>	I <sub>DDO</sub>
Outputs Disabled	L	H	H	H	High-Z	I <sub>DDO</sub>
Standby	H	x	x	x	High-Z	I <sub>DDS</sub>
	x	L	x	x	High-Z	I <sub>DDS</sub>

Note: x = don't care. H = logic high. L = logic low.

**ABSOLUTE MAXIMUM RATINGS**

SYMBOL	RATING	VALUE	UNIT
V <sub>DD</sub>	Power Supply Voltage	- 0.3 to 4.6	V
V <sub>IN</sub>	Input Voltage	- 0.3* to 4.6	V
V <sub>I/O</sub>	Input/Output Voltage	- 0.5 to V <sub>DD</sub> + 0.5	V
P <sub>D</sub>	Power Dissipation	0.8	W
T <sub>solder</sub>	Soldering Temperature (10 s)	260	°C
T <sub>strg.</sub>	Storage Temperature	- 55 to 150	°C
T <sub>opr.</sub>	Operating Temperature	- 40 to 85	°C

\* - 3.0 V when measured at a pulse width of 50 ns

**DC RECOMMENDED OPERATING CONDITIONS (Ta = -40° to 85°C)**

SYMBOL	PARAMETER	2.7 to 3.6 V			UNIT
		MIN	TYP	MAX	
V <sub>DD</sub>	Power Supply Voltage	2.7	-	3.6	V
V <sub>IH</sub>	Input High Voltage	2.2	-	V <sub>DD</sub> + 0.3	
V <sub>IL</sub>	Input Low Voltage	- 0.3*	-	0.6	
V <sub>DH</sub>	Data Retention Supply Voltage	2.0	-	3.6	

\* - 3.0 V when measured at a pulse width of 50 ns

**DC CHARACTERISTICS (Ta = -40° to 85°C, V<sub>DD</sub> = 2.7 to 3.6 V)**

SYMBOL	PARAMETER	TEST CONDITION	MIN	TYP	MAX	UNIT			
I <sub>IL</sub>	Input Leakage Current	V <sub>IN</sub> = 0 V to V <sub>DD</sub>	-	-	± 1.0	μA			
I <sub>OH</sub>	Output High Current	V <sub>OH</sub> = V <sub>DD</sub> - 0.5 V	-0.5	-	-	mA			
I <sub>OL</sub>	Output Low Current	V <sub>OL</sub> = 0.4 V	2.1	-	-	mA			
I <sub>LO</sub>	Output Leakage Current	$\overline{CE1} = V_{IH}$ or $CE2 = V_{IL}$ or $R/W = V_{IL}$ or $OE = V_{IH}$ , V <sub>OUT</sub> = 0 V to V <sub>DD</sub>	-	-	± 1.0	μA			
I <sub>DDO1</sub>	Operating Current	$\overline{CE1} = V_{IL}$ and $CE2 = V_{IH}$ and $R/W = V_{IH}$ , I <sub>OUT</sub> = 0 mA Other Input = V <sub>IH</sub> /V <sub>IL</sub>	V <sub>DD</sub> = 3 V ± 10%	Tcycle	min	-	-	35	mA
					1 μs	-	-	10	
I <sub>DDO2</sub>	Operating Current	$\overline{CE1} = 0.2$ V and $CE2 = V_{DD} - 0.2$ V $R/W = V_{DD} - 0.2$ V, I <sub>OUT</sub> = 0 mA Other Inputs = V <sub>DD</sub> - 0.2 V/0.2 V	V <sub>DD</sub> = 3.3 V ± 0.3 V	Tcycle	min	-	-	40	
					1 μs	-	-	12	
I <sub>DDO2</sub>	Operating Current	$\overline{CE1} = 0.2$ V and $CE2 = V_{DD} - 0.2$ V $R/W = V_{DD} - 0.2$ V, I <sub>OUT</sub> = 0 mA Other Inputs = V <sub>DD</sub> - 0.2 V/0.2 V	V <sub>DD</sub> = 3 V ± 10%	Tcycle	min	-	-	30	
					1 μs	-	-	5	
I <sub>DDO2</sub>	Operating Current	$\overline{CE1} = 0.2$ V and $CE2 = V_{DD} - 0.2$ V $R/W = V_{DD} - 0.2$ V, I <sub>OUT</sub> = 0 mA Other Inputs = V <sub>DD</sub> - 0.2 V/0.2 V	V <sub>DD</sub> = 3.3 V ± 0.3 V	Tcycle	min	-	-	35	
					1 μs	-	-	6	
I <sub>DDS1</sub>	Standby Current	$\overline{CE1} = V_{IH}$ or $CE2 = V_{IL}$	-	-	2	mA			
I <sub>DDS2</sub> (Note)		$\overline{CE1} = V_{DD} - 0.2$ V or $CE2 = 0.2$ V V <sub>DD</sub> = 2.0 to 3.6 V	V <sub>DD</sub> = 3 V ± 10%	Ta = 25°C	-85, -10	-	1	2.5	
	-85L, -10L				-	0.5	1.2		
	-85, -10				-	-	55		
	Ta = -40° to 85°C			-85L, -10L	-	-	35		
				-85, -10	-	1.5	3		
				-85L, -10L	-	0.7	1.4		
	V <sub>DD</sub> = 3 V		Ta = 25°C	-85, -10	-	-	60		
				-85L, -10L	-	-	40		
				-85, -10	-	1	2		
			Ta = -40° to 40°C	-85L, -10L	-	0.5	1		
				-85, -10	-	-	5		
				-85L, -10L	-	-	3		
Ta = -40° to 85°C	-85, -10	-	-	50					
	-85L, -10L	-	-	30					

Note: In standby mode with  $\overline{CE1} \geq V_{DD} - 0.2$  V, these limits are assured for the condition  $CE2 \geq V_{DD} - 0.2$  V or  $CE2 \leq 0.2$  V.

**CAPACITANCE (Ta = 25°C, f = 1 MHz)**

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = GND	10	pF
C <sub>OUT</sub>	Output Capacitance	V <sub>OUT</sub> = GND	10	

Note: This parameter is periodically sampled and is not 100% tested.

**AC CHARACTERISTICS AND OPERATING CONDITIONS** (Ta = -40° to 85°C, VDD = 2.7 to 3.6 V)

**READ CYCLE**

SYMBOL	PARAMETER	TC55V2001FI/FTI/TRI/STI/SRI				UNIT
		-85, -85L		-10, -10L		
		MIN	MAX	MIN	MAX	
t <sub>RC</sub>	Read Cycle Time	85	–	100	–	ns
t <sub>ACC</sub>	Address Access Time	–	85	–	100	
t <sub>CO1</sub>	Chip Enable (CE1) Access Time	–	85	–	100	
t <sub>CO2</sub>	Chip Enable (CE2) Access Time	–	85	–	100	
t <sub>OE</sub>	Output Enable Access Time	–	45	–	50	
t <sub>COE</sub>	Chip Enable Low to Output Active	5	–	5	–	
t <sub>OEE</sub>	Output Enable Low to Output Active	0	–	0	–	
t <sub>OD</sub>	Chip Enable High to Output High-Z	–	35	–	40	
t <sub>ODO</sub>	Output Enable High to Output High-Z	–	35	–	40	
t <sub>OH</sub>	Output Data Hold Time	10	–	10	–	

**WRITE CYCLE**

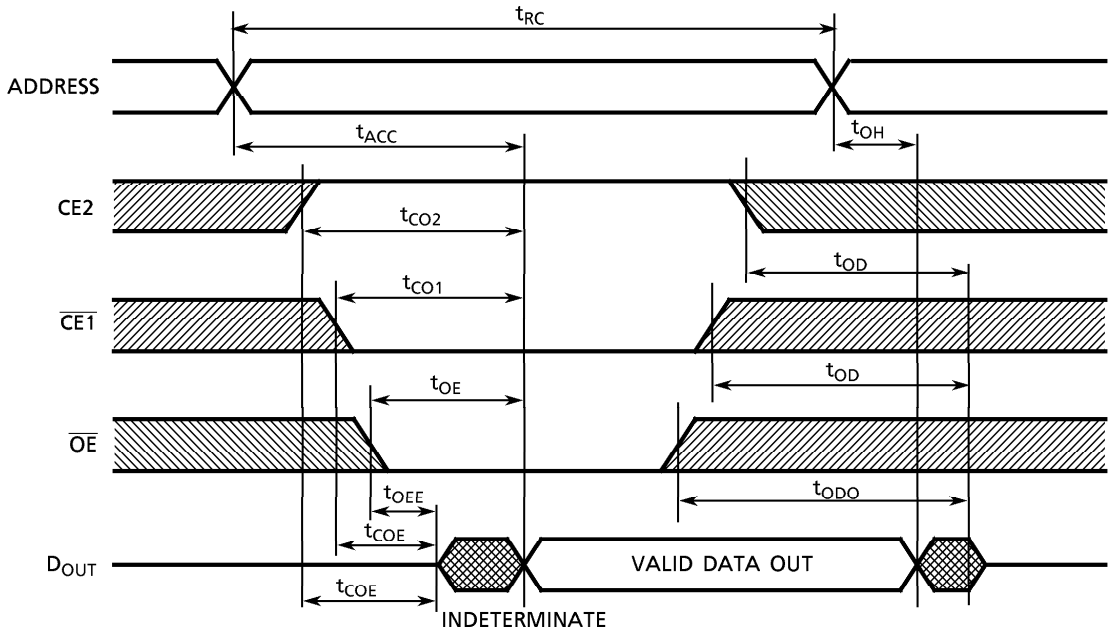
SYMBOL	PARAMETER	TC55V2001FI/FTI/TRI/STI/SRI				UNIT
		-85, -85L		-10, -10L		
		MIN	MAX	MIN	MAX	
t <sub>WC</sub>	Write Cycle Time	85	–	100	–	ns
t <sub>WP</sub>	Write Pulse Width	60	–	60	–	
t <sub>CW</sub>	Chip Enable to End of Write	75	–	80	–	
t <sub>AS</sub>	Address Setup Time	0	–	0	–	
t <sub>WR</sub>	Write Recovery Time	0	–	0	–	
t <sub>ODW</sub>	R/W Low to Output High-Z	–	35	–	40	
t <sub>OEW</sub>	R/W High to Output Active	0	–	0	–	
t <sub>DS</sub>	Data Setup Time	35	–	40	–	
t <sub>DH</sub>	Data Hold Time	0	–	0	–	

**AC TEST CONDITIONS**

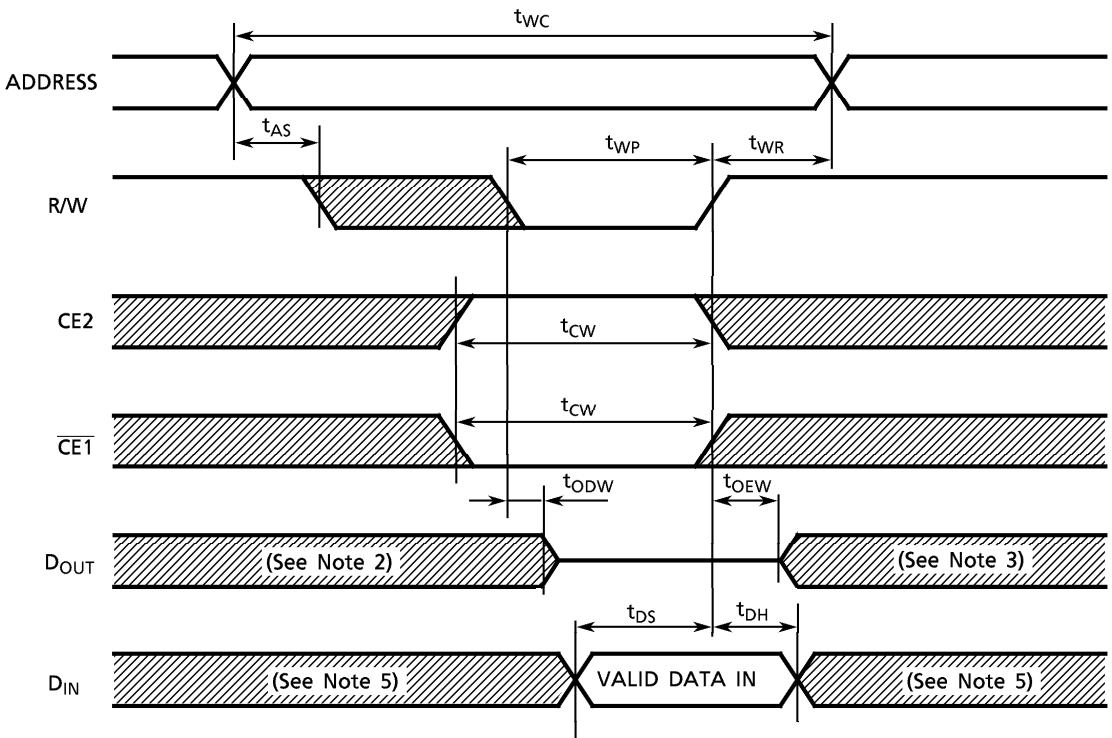
Output load: 100 pF + one TTL gate  
 Input pulse level: 0.4 V, 2.4 V  
 Timing measurements: 1.5 V  
 Reference level: 1.5 V  
 t<sub>R</sub>, t<sub>F</sub>: 5 ns

**TIMING DIAGRAMS**

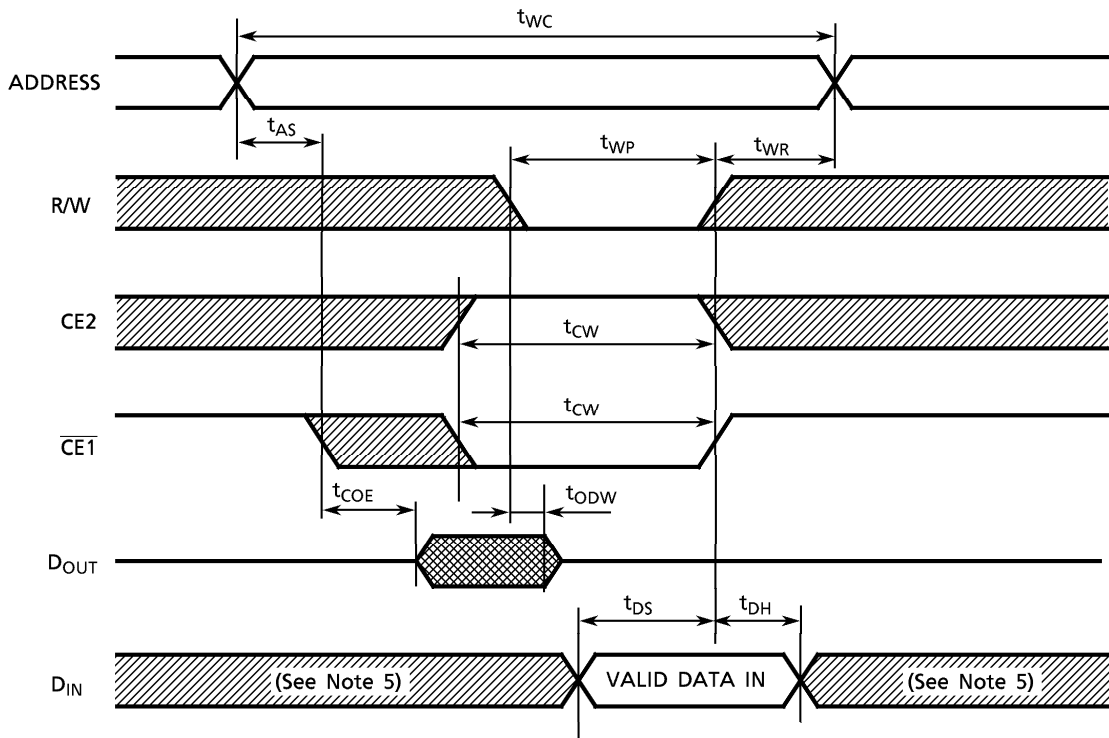
**READ CYCLE (See Note 1)**



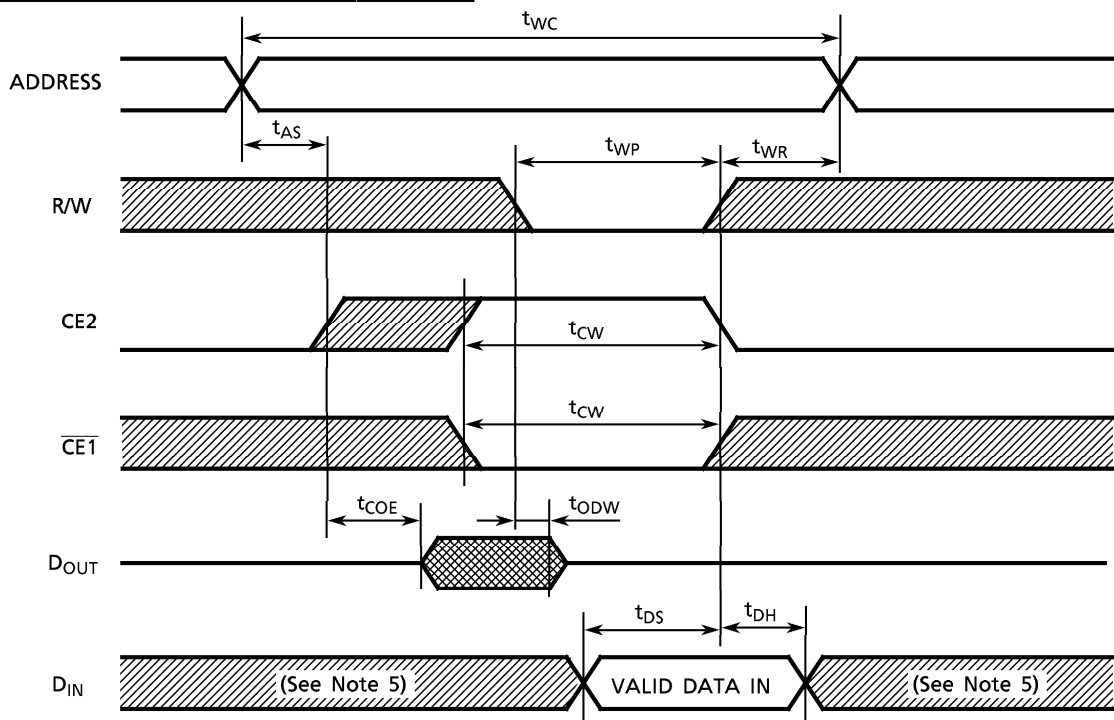
**WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)**



WRITE CYCLE 2 (CE1 CONTROLLED) (See Note 4)



WRITE CYCLE 3 (CE2 CONTROLLED) (See Note 4)



Note: (1) R/W remains HIGH for the read cycle.

(2) If  $\overline{CE1}$  goes LOW (or CE2 goes HIGH) coincident with or after R/W goes LOW, the outputs will remain at high impedance.

(3) If  $\overline{CE1}$  goes HIGH (or CE2 goes LOW) coincident with or before R/W goes HIGH, the outputs will remain at high impedance.

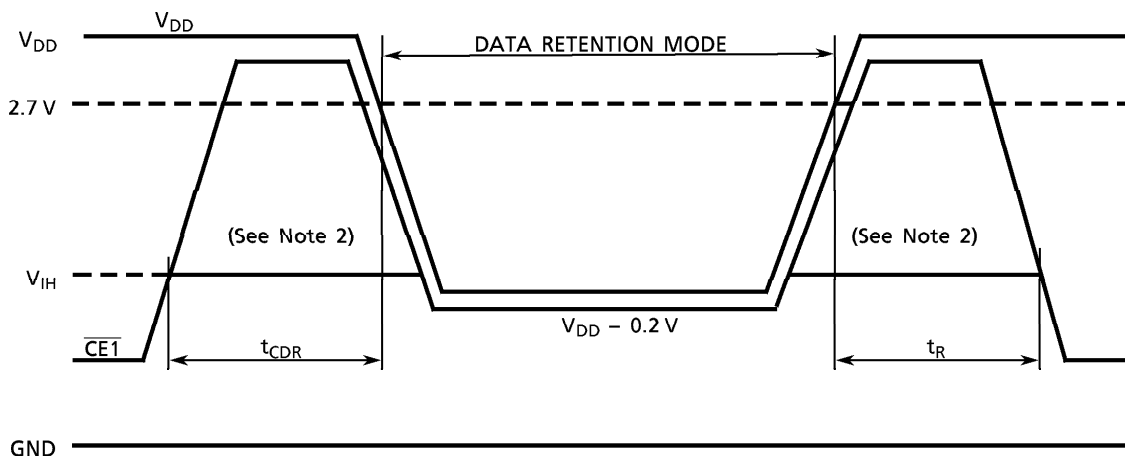
(4) If  $\overline{OE}$  is HIGH during the write cycle, the outputs will remain at high impedance.

(5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

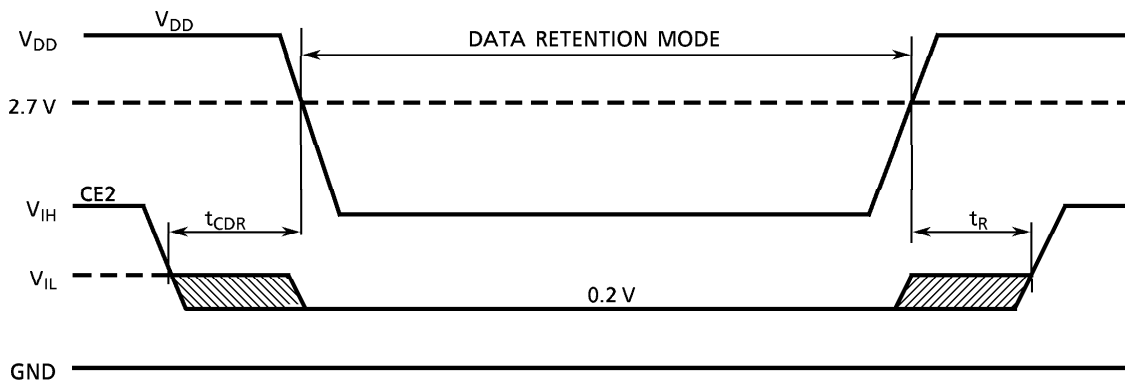
**DATA RETENTION CHARACTERISTICS (Ta = -40° to 85°C)**

SYMBOL	PARAMETER		MIN	TYP	MAX	UNIT	
V <sub>DH</sub>	Data Retention Supply Voltage		2.0	-	3.6	V	
I <sub>DD2</sub>	Standby Current	V <sub>DH</sub> = 3.0V	Ta = -40° to 40°C	-85, -10	-	5	μA
				-85L, -10L	-	3	
		V <sub>DH</sub> = 3.6V	Ta = -40° to 85°C	-85, -10	-	50	
				-85L, -10L	-	30	
t <sub>CDR</sub>	Chip Deselect to Data Retention Mode Time		0	-	-	nS	
t <sub>R</sub>	Recovery Time		5	-	-	mS	

**CE1 CONTROLLED DATA RETENTION MODE (See Note 1)**



CE2 CONTROLLED DATA RETENTION MODE (See Note 3)

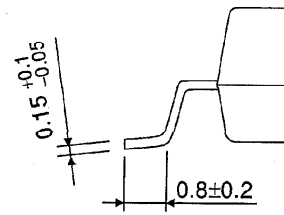
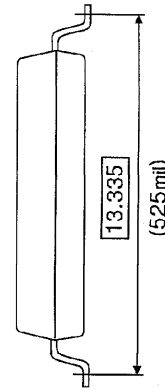
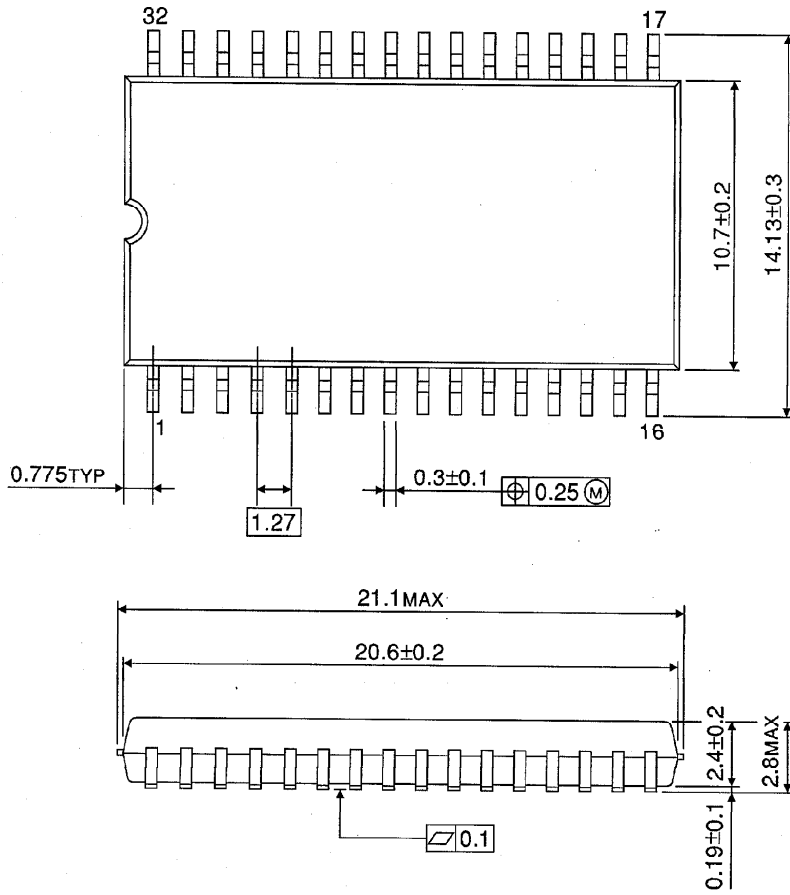


- Note: (1) In  $\overline{CE1}$  controlled data retention mode, minimum standby current mode is entered when  $CE2 \leq 0.2\text{ V}$  or  $CE2 \geq V_{DD} - 0.2\text{ V}$ .
- (2) When  $\overline{CE1}$  is operating at the  $V_{IH}$  level (2.2 V), the operating current is given by  $I_{DDs1}$  during the transition of  $V_{DD}$  from 3.6 to 2.4 V.
- (3) In CE2 controlled data retention mode, minimum standby current mode is entered when  $CE2 \leq 0.2\text{ V}$ .



**PACKAGE DIMENSIONS (SOP32-P-525-1.27)**

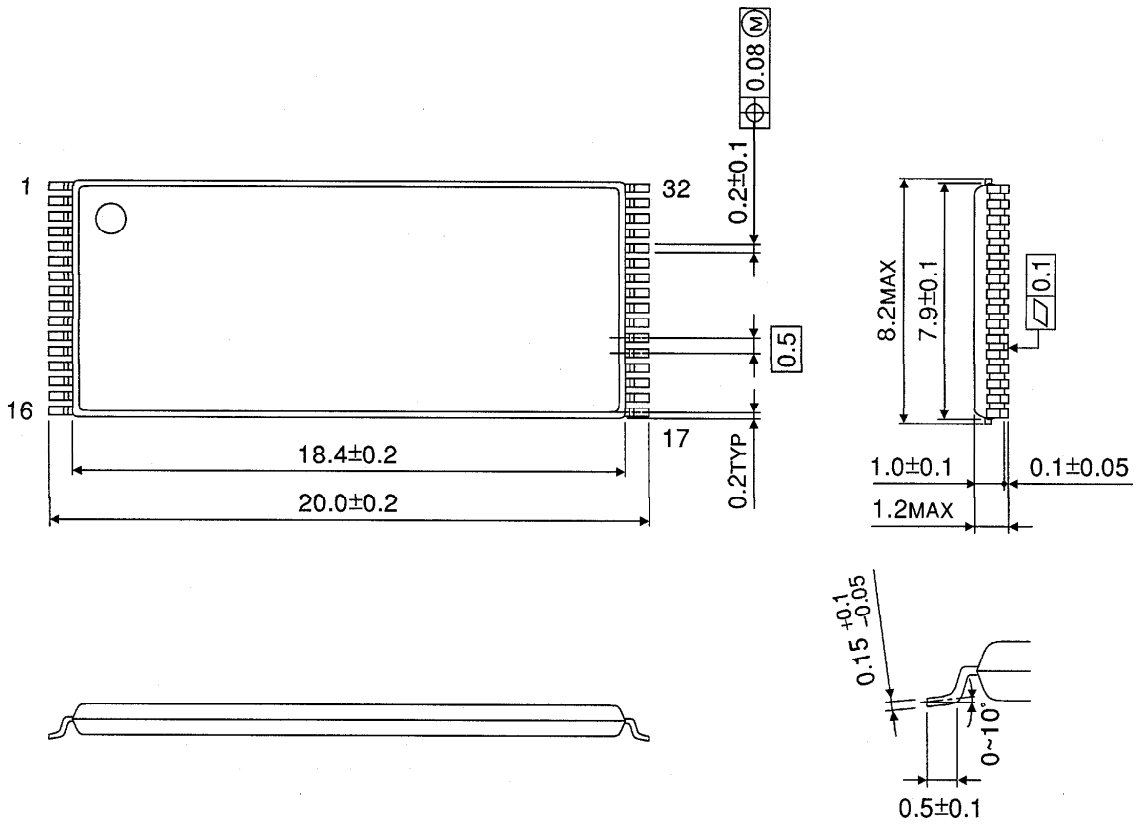
Units in mm



Weight: 1.06 g (typ)

PACKAGE DIMENSIONS (TSOP I 32-P-0820-0.50)

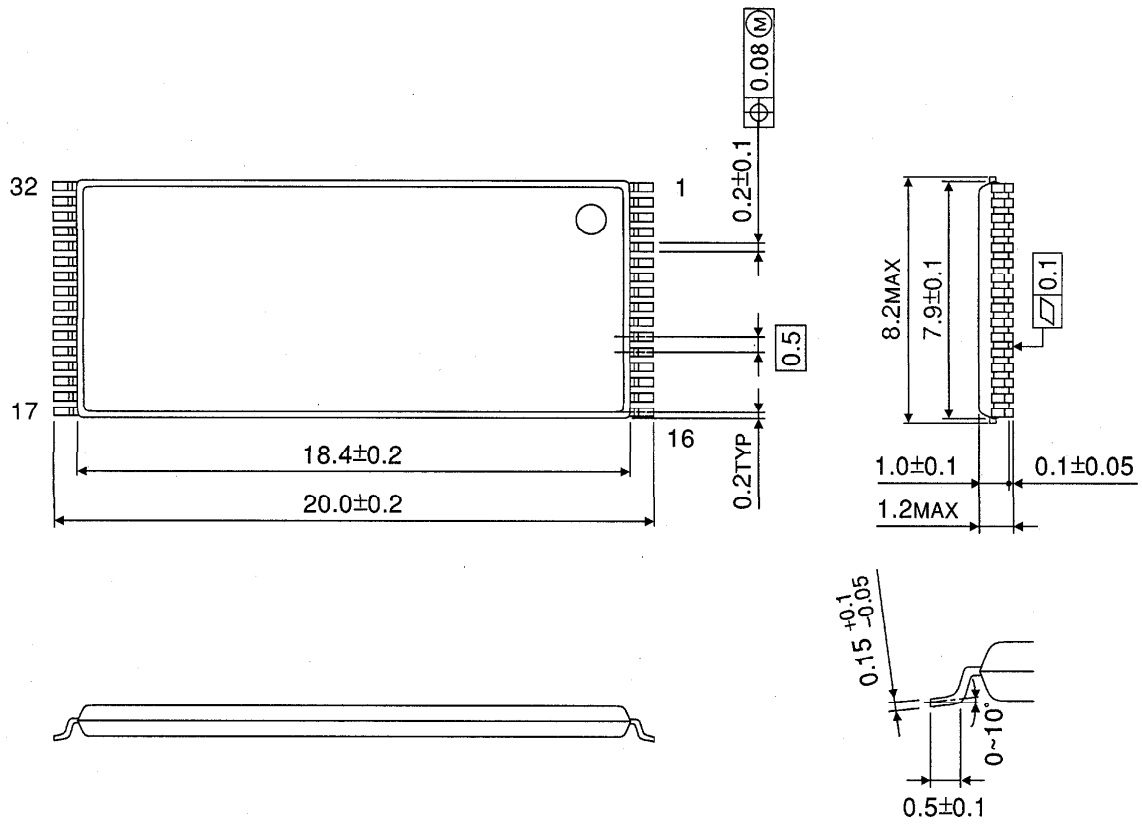
Units in mm



Weight: 0.34 g (typ)

PACKAGE DIMENSIONS (TSOP I 32-P-0820-0.50A)

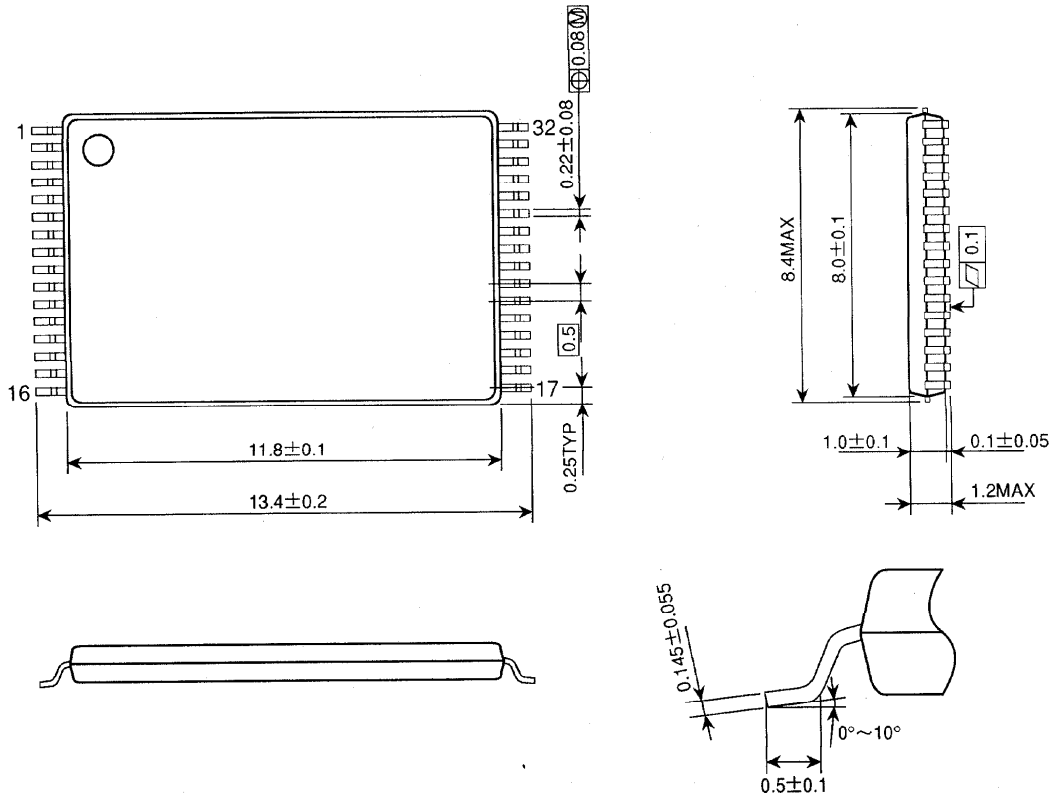
Units in mm



Weight: 0.34 g (typ)

PACKAGE DIMENSIONS (TSOP I 32-P-0.50)

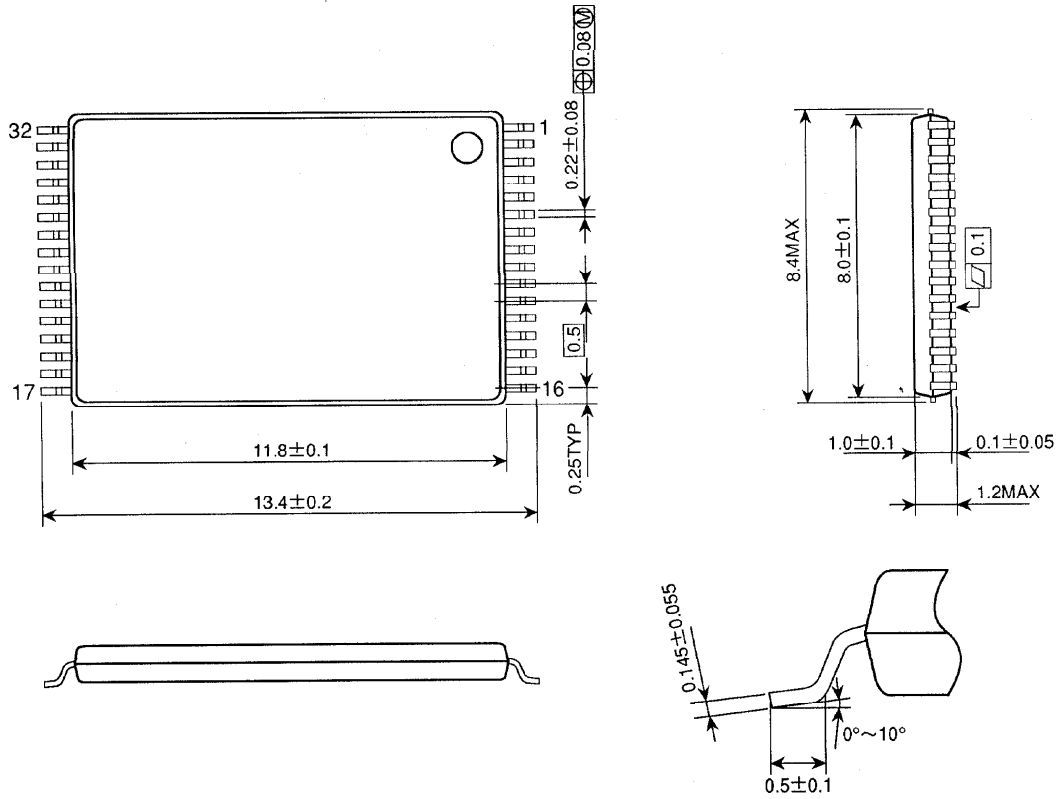
Units in mm



Weight: 0.24 g (typ)

PACKAGE DIMENSIONS (TSOP I 32-P-0.50A)

Units in mm



Weight: 0.24 g (typ)